

Search Notes

Application/Control No.

10/698,169

Examiner

Anh D. Mai

Applicant(s)/Patent under
Reexamination

ARONOWITZ ET AL.

Art Unit

2814

SEARCHED

| Class | Subclass | Date | Examiner |
|-------|-----------------------------|------------|----------|
| 257 | 288; 324 325; 410 411 | 12/22/2004 | A.M |
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INTERFERENCE SEARCHED

| Class | Subclass | Date | Examiner |
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**SEARCH NOTES
(INCLUDING SEARCH STRATEGY)**

| | DATE | EXMR |
|--|----------|------|
| EAST (all) * Inventors *CCLS * gate dielectric and ((zirconium or Zr) or (hafnium or Hf) or aluminum or Al)) and silicon oxide and gate and semiconductor and source and drain and circuit and trapp\$. | 12/22/04 | A.M |
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